

ABSTRACT OF THE DISCLOSURE

In a semiconductor thin film forming system for modifying a predetermined region of a semiconductor thin film by exposing the semiconductor thin film to a projected light patterned through a pattern formed on a photo mask, the system includes a mechanism (opt20') for uniformizing the light for exposure in a predetermined area on the photo mask. This system can provide a crystallized silicon film having a trap state density less than 10^{12} cm^{-2} and can provide a silicon-insulating film interface exhibiting a low interface state density.

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